# SQS486CENW

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**Vishay Siliconix** 

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET



Marking code: Q044

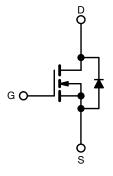
PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0051
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0073
I <sub>D</sub> (A)	18
Configuration	Single
Package	PowerPAK 1212-8W

#### FEATURES

- TrenchFET<sup>®</sup> Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



COMPLIANT HALOGEN FREE



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise notec	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	v	
Gate-source voltage		V <sub>GS</sub>	± 20	v	
Continuous drain current <sup>a</sup>	T <sub>C</sub> = 25 °C	1-	18		
Continuous drain current -	T <sub>C</sub> = 125 °C	I <sub>D</sub>	18		
Continuous source current (diode conductio	I <sub>S</sub>	18	А		
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	72		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	23.5		
Single pulse avalanche energy		E <sub>AS</sub>	27.6	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	PD	62.5	w	
Maximum power dissipation -	T <sub>C</sub> = 125 °C	FD	20	vv	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	81	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	2.4	C/ VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

S20-0824-Rev. A, 26-Oct-2020 1 Document Number: 78989 For technical questions, contact: <u>automostechsupport@vishay.com</u>

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<b>SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C, ui PARAMETER	SYMBOL	-	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	01111202					in du		
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	40	-	-		
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	: V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.2	1.7	2.2	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		V <sub>GS</sub> = 0 V	$V_{DS} = 40 \text{ V}, \text{ T}_{\text{J}} = 175 ^{\circ}\text{C}$	-	-	150		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	15	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0041	0.0051		
	P	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0075	0	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0087	Ω	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 8 A	-	0.0060	0.0073	1	
Forward transconductance b	<b>g</b> <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 10 A	-	68	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>			-	2098	2950		
Output capacitance	Coss	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	624	900	pF	
Reverse transfer capacitance	C <sub>rss</sub>			-	40	56		
Total gate charge <sup>c</sup>	Qg			-	35.2	53		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 4 \text{ A}$	-	6.1	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	6	-		
Gate resistance	Rg	f = 1 MHz		0.81	1.63	2.45	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	14	22		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 5 $\Omega$		-	7	12	ns	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ 4 A, V	$V_{ m GEN}$ = 10 V, R <sub>g</sub> = 1 $\Omega$	-	43	65	ns	
Fall time <sup>c</sup>	t <sub>f</sub>			-	13	20		
Source-Drain Diode Ratings and Charact	eristic <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	72	Α	
Forward voltage	$V_{SD}$	I <sub>F</sub> =	10 A, $V_{GS} = 0 V$	-	0.79	1.1	V	
Body diode reverse recovery time	t <sub>rr</sub>			-	32	64	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>	- I <sub>F</sub> = 5 A, di/dt = 100 A/μs		-	25	50	nC	
Reverse recovery fall time	t <sub>a</sub>			-	16	-	ns	
Reverse recovery rise time	t <sub>b</sub>			-	16	-		
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-1.33	-	А	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

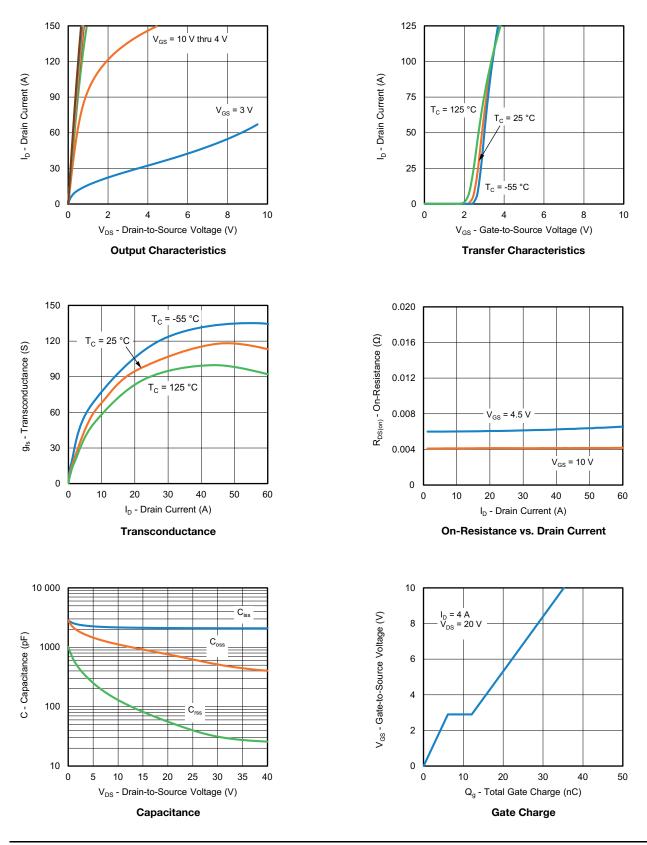
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



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3 stions contact: automostechsupp

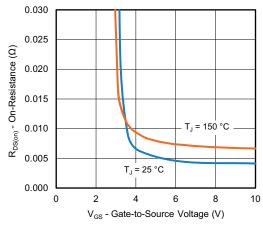
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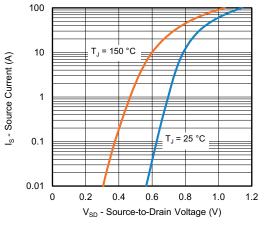
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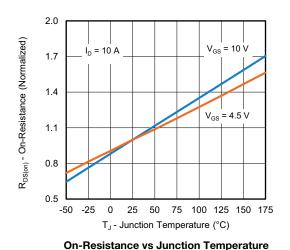
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

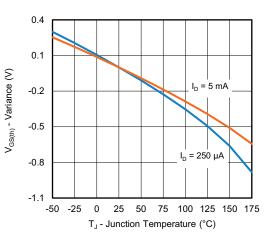


On-Resistance vs. Gate-to-Source Voltage

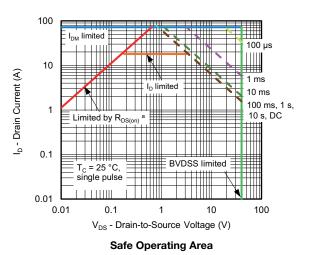


Source Drain Diode Forward Voltage





Threshold Voltage



58 V<sub>DS</sub> - Drain-to-Source Voltage (V) 1 mA 56 I<sub>D</sub> 54 52 50 48 -25 -50 0 25 50 75 100 125 150 175 T<sub>1</sub> - Junction Temperature (°C)

Drain Source Breakdown vs. Junction Temperature

Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

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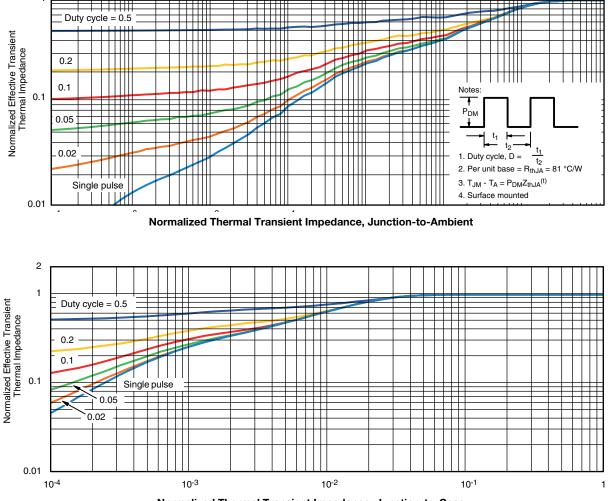


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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?78989.

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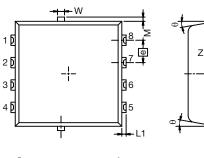


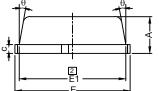
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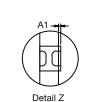
# PowerPAK<sup>®</sup> 1212-8W Case Outline

Δ2

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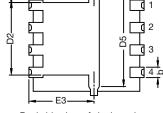




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Б



E2

E4

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Notes
1 Inch will govern

 Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4	0.47 typ.			0.0185 typ.			
D5	2.3 typ.			0.090 typ.			
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4	0.34 typ.				0.013 typ.		
е	0.65 BSC.			0.026 BSC			
К		0.86 typ.		0.034 typ.			
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			
N: C15-1530-R	ev. B, 16-Nov-15						

Backside view of single pad



## RECOMMENDED MINIMUM PADS FOR PowerPAK<sup>®</sup> 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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